

**AMENDMENTS**

Please amend claim 2, claim 10 and claim 16 as follows:

2. (amended) The method of claim 1 wherein a thickness of the patterned photoresist layer and a thickness of the oxygen containing plasma etchable microelectronics layer are each selected [such] to provide that:

the patterned photoresist layer is completely etched from the patterned hard mask layer;

the oxygen containing plasma etchable microelectronics layer is completely etched to form

a the patterned oxygen containing plasma etchable microelectronics layer; and

there is attenuated lateral etching of the patterned oxygen containing plasma etchable microelectronics layer.

10. The method of claim 9 wherein a thickness of the patterned photoresist layer and a thickness of the oxygen containing plasma etchable microelectronics dielectric layer are each selected [such] to provide that:

the patterned photoresist layer is completely etched from the patterned hard mask layer;

a<sup>2</sup> the oxygen containing plasma etchable microelectronics dielectric layer is completely etched to form the patterned oxygen containing plasma etchable microelectronics dielectric layer; and

there is attenuated lateral etching of the patterned oxygen containing plasma etchable microelectronics dielectric layer.